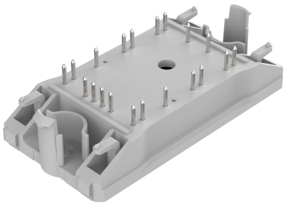
10-FZ07NIA100S502-P927F58
datasheet

***flow*NPC 0** **1200 V / 100 A**

Features

- High switching frequency
- High efficiency
- Easy controllability

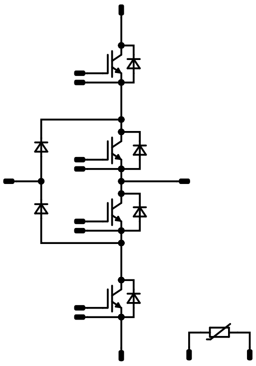
flow 0 12 mm housing



Target applications

- Solar Inverters
- UPS

Schematic



Types

- 10-FZ07NIA100S502-P927F58

Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Buck Switch				
Collector-emitter voltage	V_{CES}		650	V
Collector current	I_C	$T_j = T_{jmax}$ T_s = 80 °C	82	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}	300	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ T_s = 80 °C	117	W
Gate-emitter voltage	V_{GES}		±20	V
Maximum junction temperature	T_{jmax}		175	°C
Buck Diode				
Peak repetitive reverse voltage	V_{RRM}		650	V
Continuous (direct) forward current	I_F	$T_j = T_{jmax}$ T_s = 80 °C	70	A
Repetitive peak forward current	I_{FRM}	t_p limited by T_{jmax}	200	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ T_s = 80 °C	95	W
Maximum junction temperature	T_{jmax}		175	°C
Boost Switch				
Collector-emitter voltage	V_{CES}		650	V
Collector current	I_C	$T_j = T_{jmax}$ T_s = 80 °C	82	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}	300	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ T_s = 80 °C	117	W
Gate-emitter voltage	V_{GES}		±20	V
Maximum junction temperature	T_{jmax}		175	°C

Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	**Symbol**	**Conditions**	**Value**	**Unit**
Boost Diode				
Peak repetitive reverse voltage	V_{RRM}		650	V
Continuous (direct) forward current	I_F	$T_j = T_{jmax}$ T_s = 80 °C	70	A
Repetitive peak forward current	I_{FRM}	t_p limited by T_{jmax}	200	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ T_s = 80 °C	95	W
Maximum junction temperature	T_{jmax}		175	°C
Boost Sw. Inv. Diode				
Peak repetitive reverse voltage	V_{RRM}		650	V
Continuous (direct) forward current	I_F	$T_j = T_{jmax}$ T_s = 80 °C	70	A
Repetitive peak forward current	I_{FRM}	t_p limited by T_{jmax}	200	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ T_s = 80 °C	95	W
Maximum junction temperature	T_{jmax}		175	°C
Module Properties				
Thermal Properties				
Storage temperature	T_{stg}		-40…+125	°C
Operation temperature under switching condition	T_{jop}		-40…+(T_{jmax} - 25)	°C
Isolation Properties				
Isolation voltage	V_{isol}	DC Test Voltage* t_p = 2 s	6000	V
Isolation voltage	V_{isol}	AC Voltage t_p = 1 min	2500	V
Creepage distance			min. 12,7	mm
Clearance			9,15	mm
Comparative Tracking Index	CTI		≥ 200	

*100 % tested in production

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Buck Switch										
Static										
Gate-emitter threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}$			0,001	25	3,2	4	4,8	V
Collector-emitter saturation voltage	V_{CEsat}		15		100	25 125 150		1,39 1,48 1,51	1,75	V
Collector-emitter cut-off current	I_{CES}		0	650		25			100	μA
Gate-emitter leakage current	I_{GES}		20	0		25			200	nA
Internal gate resistance	r_g							None		Ω
Input capacitance	C_{ies}	f = 1 Mhz	0	25		25		6200		pF
Output capacitance	C_{oes}							176		pF
Reverse transfer capacitance	C_{res}							24		pF
Gate charge	Q_g	V_{CC} = 520 V	15		100	25		240		nC
Thermal										
Thermal resistance junction to sink*	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						0,81		K/W

*Only valid with pre-applied Vincotech thermal interface material.

Parameter	Symbol	Conditions	V_{GE} [V]	V_{CE} [V]	I_C [A]	T_j [°C]	Min	Typ	Max	Unit
Dynamic										
Turn-on delay time	$t_{d(on)}$	R_{gon} = 4 Ω R_{goff} = 4 Ω	±15	350	100	25 125 150		64,5 65,5 66		ns
Rise time	t_r					25 125 150		8,5 9,5 10		ns
Turn-off delay time	$t_{d(off)}$					25 125 150		87,5 105,5 110		ns
Fall time	t_f					25 125 150		13,94 22,72 50,59		ns
Turn-on energy (per pulse)	E_{on}	Q_{rFWD}=3,18 μC Q_{rFWD}=5,91 μC Q_{rFWD}=6,72 μC				25 125 150		0,981 1,34 1,37		mWs
Turn-off energy (per pulse)	E_{off}					25 125 150		0,676 1,19 1,37		mWs

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Buck Diode										
Static										
Forward voltage	V_F				100	25 125 150		1,6 1,58 1,57	1,92	V
Reverse leakage current	I_R	V_r = 650 V				25			5,3	µA
Thermal										
Thermal resistance junction to sink*	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1		K/W
*Only valid with pre-applied Vincotech thermal interface material.										
Dynamic										
Peak recovery current	I_{RRM}	di/dt=9150 A/µs di/dt=7920 A/µs di/dt=7488 A/µs	±15	350	100	25 125 150		112,21 137,32 144,14		A
Reverse recovery time	t_{rr}					25 125 150		60,32 98,6 109,83		ns
Recovered charge	Q_r					25 125 150		3,18 5,91 6,72		µC
Reverse recovered energy	E_{rec}					25 125 150		0,486 1 1,18		mWs
Peak rate of fall of recovery current	$(di_{rf}/dt)_{max}$					25 125 150		8293 2829 3138		A/µs

Characteristic Values

Parameter	Symbol	Conditions	V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	Unit
Boost Switch										
Static										
Gate-emitter threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}$			0,001	25	3,2	4	4,8	V
Collector-emitter saturation voltage	V_{CEsat}		15		100	25 125 150		1,39 1,48 1,51	1,75	V
Collector-emitter cut-off current	I_{CES}		0	650		25			100	µA
Gate-emitter leakage current	I_{GES}		20	0		25			200	nA
Internal gate resistance	r_g							None		Ω
Input capacitance	C_{ies}	f = 1 Mhz	0	25		25		6200		pF
Output capacitance	C_{oes}							176		pF
Reverse transfer capacitance	C_{res}							24		pF
Gate charge	Q_g	V_{CC} = 520 V	15		100	25		240		nC
Thermal										
Thermal resistance junction to sink*	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						0,81		K/W
Dynamic										
Turn-on delay time	$t_{d(on)}$	R_{gon} = 4 Ω R_{goff} = 4 Ω	±15	350	100	25 125 150		63,68 64,96 65,6		ns
Rise time	t_r					25 125 150		12,96 15,2 15,36		ns
Turn-off delay time	$t_{d(off)}$					25 125 150		74,72 92,48 96,8		ns
Fall time	t_f					25 125 150		11,99 32,11 35,87		ns
Turn-on energy (per pulse)	E_{on}	Q_{rFWD}=2,6 µC Q_{rFWD}=5,44 µC Q_{rFWD}=6,33 µC				25 125 150		0,756 0,97 1,02		mWs
Turn-off energy (per pulse)	E_{off}					25 125 150		1,14 1,8 1,96		mWs

*Only valid with pre-applied Vincotech thermal interface material.

Characteristic Values

Parameter	Symbol	Conditions	V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Values Min	Typ	Max	Unit
Boost Diode										
Static										
Forward voltage	V_F				100	25 125 150		1,6 1,58 1,57	1,92	V
Reverse leakage current	I_R	V_r = 650 V				25			5,3	µA
Thermal										
Thermal resistance junction to sink*	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1		K/W

*Only valid with pre-applied Vincotech thermal interface material.

Dynamic										
Peak recovery current	I_{RRM}	d*i*/d*t*=5941 A/µs d*i*/d*t*=5631 A/µs d*i*/d*t*=5557 A/µs	±15	350	100	25 125 150		68,01 95,94 103,75		A
Reverse recovery time	t_{rr}					25 125 150		105,58 154,58 174,64		ns
Recovered charge	Q_r					25 125 150		2,6 5,44 6,33		µC
Reverse recovered energy	E_{rec}					25 125 150		0,701 1,52 1,78		mWs
Peak rate of fall of recovery current	$(di_{rf}/dt)_{max}$					25 125 150		2647 2417 2609		A/µs

Characteristic Values

Parameter	**Symbol**	**Conditions**					**Values**			**Unit**
			V_{GE} **[V]** V_{GS} **[V]**	V_{CE} **[V]** V_{DS} **[V]** V_F **[V]**	I_C **[A]** I_D **[A]** I_F **[A]**	T_j **[°C]**	**Min**	**Typ**	**Max**	
Boost Sw. Inv. Diode										
Static										
Forward voltage	V_F				100	25 125 150		1,6 1,58 1,57	1,92	V
Reverse leakage current	I_R	V_r = 650 V				25			5,3	µA
Thermal										
Thermal resistance junction to sink*	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1		K/W

*Only valid with pre-applied Vincotech thermal interface material.

Thermistor

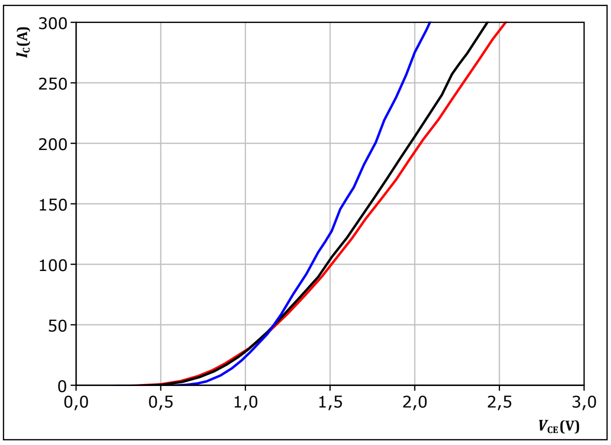
Static										
Rated resistance	R					25		22		kΩ
Deviation of R_{100}	$\Delta_{R/R}$	R_{100} = 1484 Ω				100	-5		5	%
Power dissipation	P							5		mW
Power dissipation constant	d					25		1,5		mW/K
B-value	$B_{(25/50)}$	Tol. ±1 %						3962		K
B-value	$B_{(25/100)}$	Tol. ±1 %						4000		K
Vincotech Thermistor Reference									I	

Buck Switch Characteristics

figure 1. **IGBT**

Typical output characteristics

I_C = f(V_{CE})



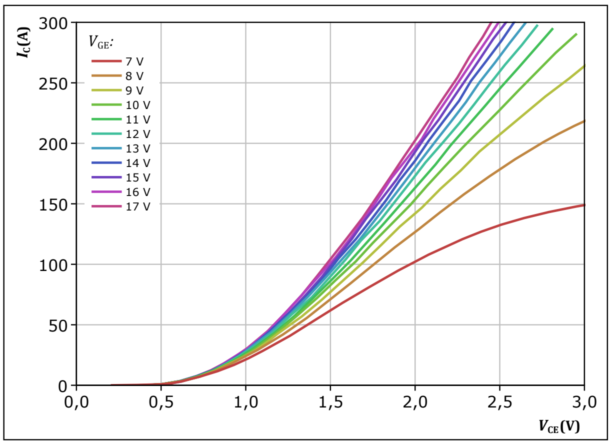
t_p = 250 µs
V_{GE} = 15 V

T_j:
25 °C
125 °C
150 °C

figure 2. **IGBT**

Typical output characteristics

I_C = f(V_{CE})

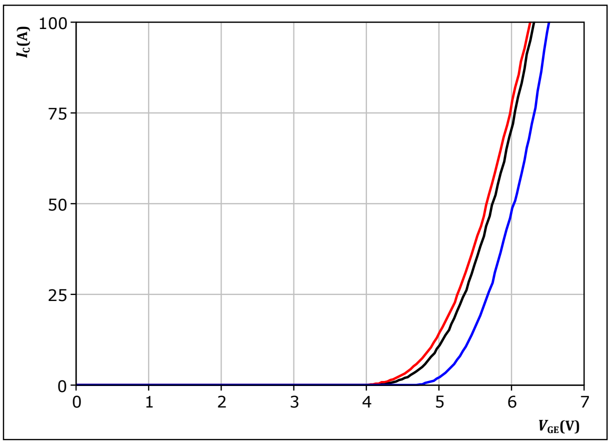


t_p = 250 µs
T_j = 150 °C
V_{GE} from 7 V to 17 V in steps of 1 V

figure 3. **IGBT**

Typical transfer characteristics

I_C = f(V_{GE})



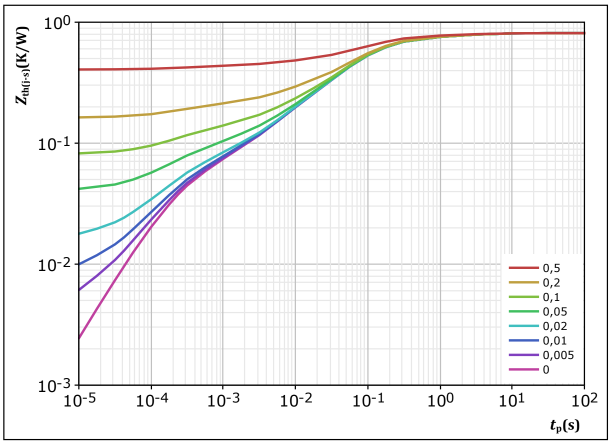
t_p = 250 µs
V_{CE} = 10 V

T_j:
25 °C
125 °C
150 °C

figure 4. **IGBT**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)}$ = f(t_p)



D = t_p / T
$R_{th(j-s)}$ = 0,812 K/W

IGBT thermal model values

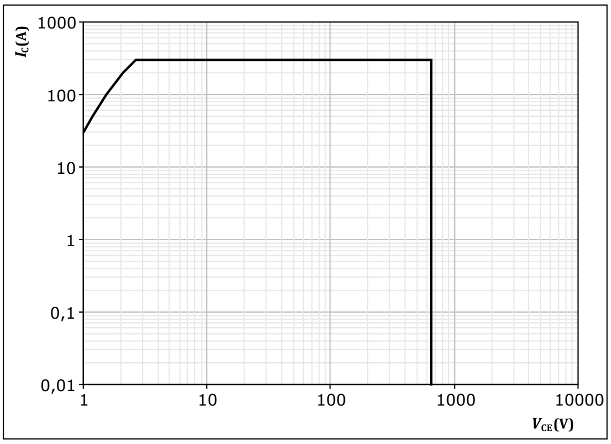
R (K/W)	τ (s)
4,67E-02	3,86E+00
8,18E-02	7,09E-01
3,18E-01	1,25E-01
2,26E-01	4,22E-02
8,12E-02	5,84E-03
2,54E-02	5,78E-04
3,27E-02	1,79E-04

Buck Switch Characteristics

figure 5. **IGBT**

Safe operating area

I_C = f(V_{CE})



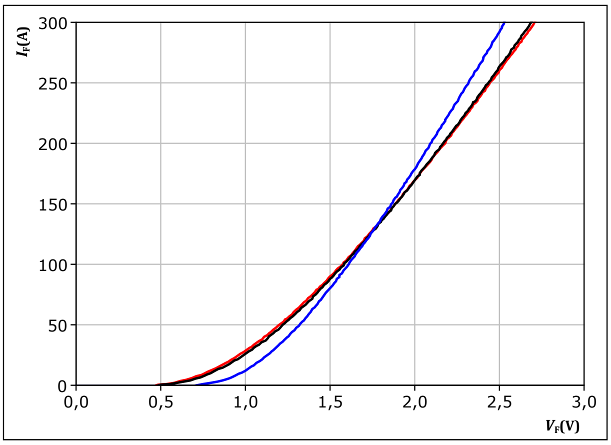
D = single pulse
T_s = 80 °C
V_{GE} = 15 V
T_j = T_{jmax}

Buck Diode Characteristics

figure 6. **FWD**

Typical forward characteristics

I_F = f(V_F)



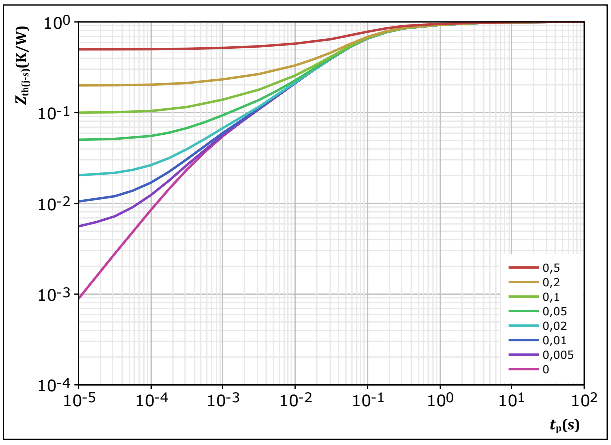
t_p = 250 µs

T_j:
- 25 °C
- 125 °C
- 150 °C

figure 7. **FWD**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)}$ = f(t_p)



D = t_p / T

$R_{th(j-s)}$ = 0,997 K/W

IGBT thermal model values

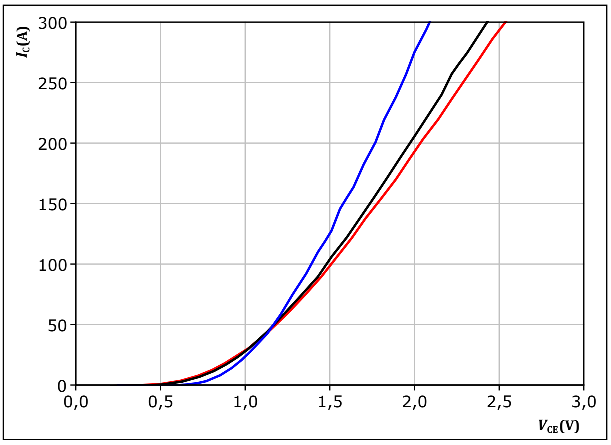
R (K/W)	τ (s)
4,57E-02	5,23E+00
1,09E-01	8,02E-01
3,92E-01	1,26E-01
3,47E-01	3,68E-02
7,19E-02	4,16E-03
3,26E-02	5,44E-04

Boost Switch Characteristics

figure 8. **IGBT**

Typical output characteristics

I_C = f(V_{CE})



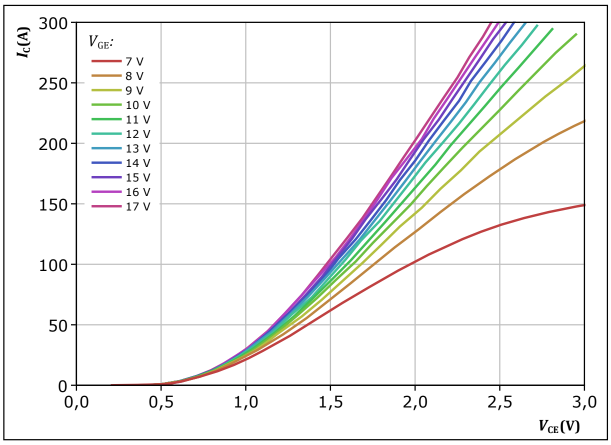
t_p = 250 µs
V_{GE} = 15 V

T_j:
25 °C
125 °C
150 °C

figure 9. **IGBT**

Typical output characteristics

I_C = f(V_{CE})

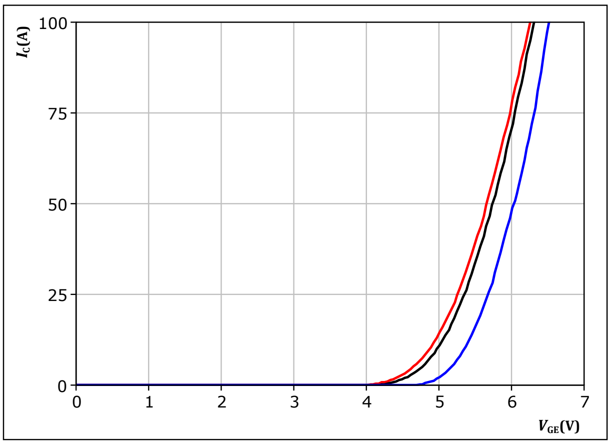


t_p = 250 µs
T_j = 150 °C
V_{GE} from 7 V to 17 V in steps of 1 V

figure 10. **IGBT**

Typical transfer characteristics

I_C = f(V_{GE})



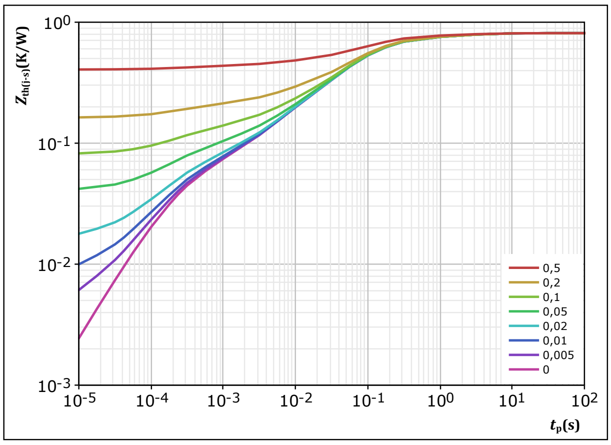
t_p = 250 µs
V_{CE} = 10 V

T_j:
25 °C
125 °C
150 °C

figure 11. **IGBT**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)}$ = f(t_p)



D = t_p / T
$R_{th(j-s)}$ = 0,812 K/W

IGBT thermal model values

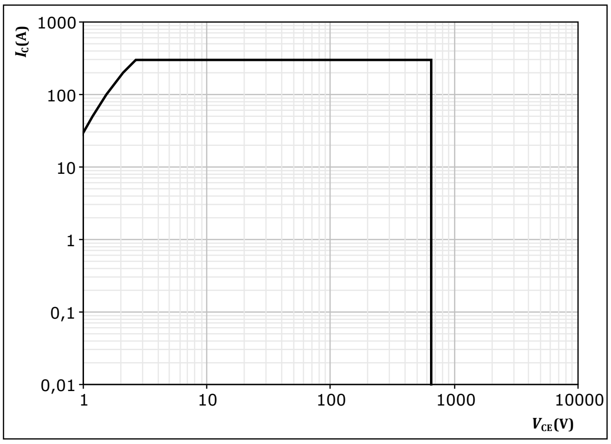
R (K/W)	τ (s)
4,67E-02	3,86E+00
8,18E-02	7,09E-01
3,18E-01	1,25E-01
2,26E-01	4,22E-02
8,12E-02	5,84E-03
2,54E-02	5,78E-04
3,27E-02	1,79E-04

Boost Switch Characteristics

figure 12. **IGBT**

Safe operating area

I_C = f(V_{CE})



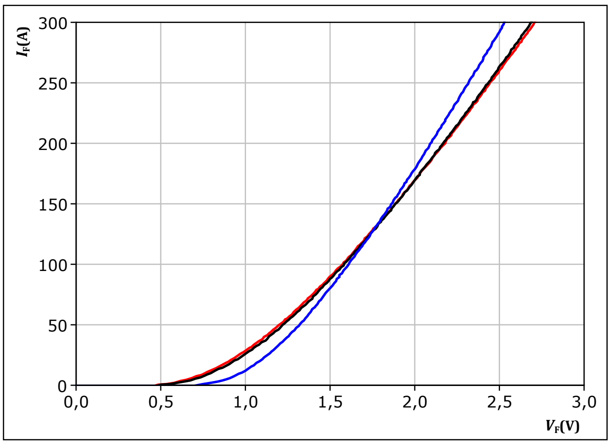
D =	single pulse	
T_s =	80	°C
V_{GE} =	15	V
T_j =	T_{jmax}	

Boost Diode Characteristics

figure 13. **FWD**

Typical forward characteristics

I_F = f(V_F)



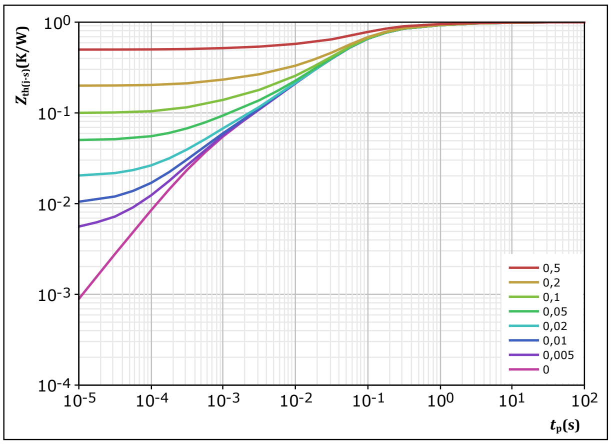
t_p = 250 μs

T_j:
25 °C
125 °C
150 °C

figure 14. **FWD**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)}$ = f(t_p)



D = t_p / T

$R_{th(j-s)}$ = 0,997 K/W

IGBT thermal model values

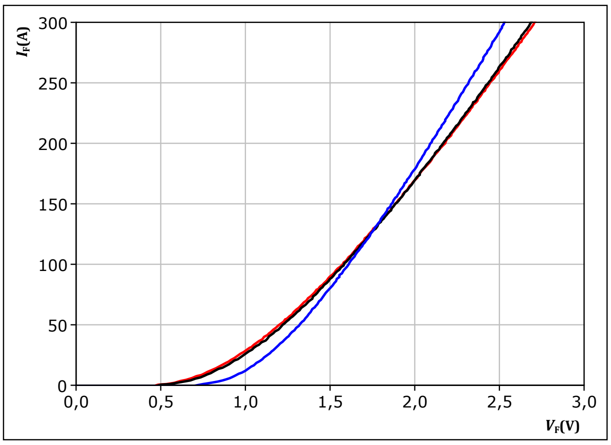
R (K/W)	τ (s)
4,57E-02	5,23E+00
1,09E-01	8,02E-01
3,92E-01	1,26E-01
3,47E-01	3,68E-02
7,19E-02	4,16E-03
3,26E-02	5,44E-04

Boost Sw. Inv. Diode Characteristics

figure 15. **FWD**

Typical forward characteristics

I_F = f(V_F)



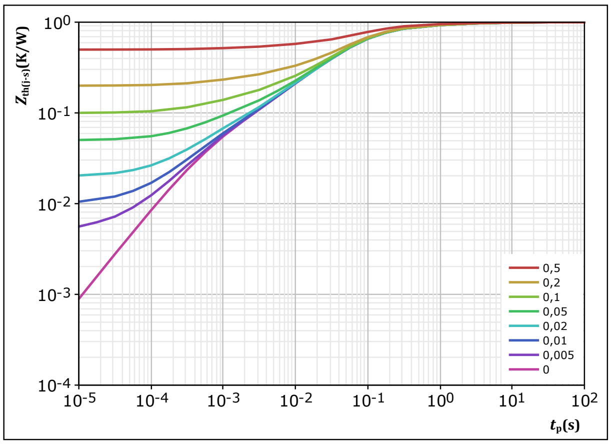
t_p = 250 μs

T_j:
- 25 °C
- 125 °C
- 150 °C

figure 16. **FWD**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)}$ = f(t_p)



D = t_p / T

$R_{th(j-s)}$ = 0,997 K/W

IGBT thermal model values

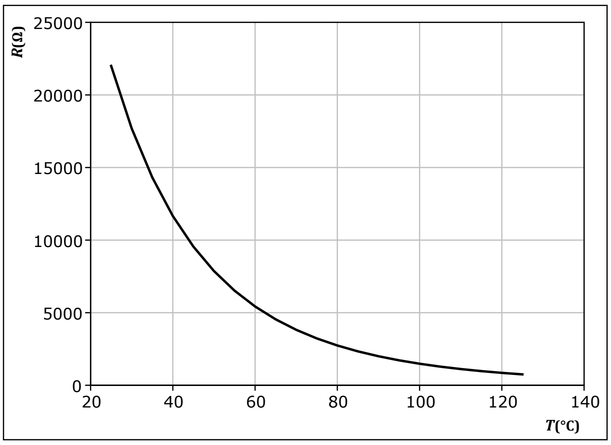
R (K/W)	τ (s)
4,57E-02	5,23E+00
1,09E-01	8,02E-01
3,92E-01	1,26E-01
3,47E-01	3,68E-02
7,19E-02	4,16E-03
3,26E-02	5,44E-04

Thermistor Characteristics

figure 17. **Thermistor**

Typical NTC characteristic as function of temperature

R_T = f(T)

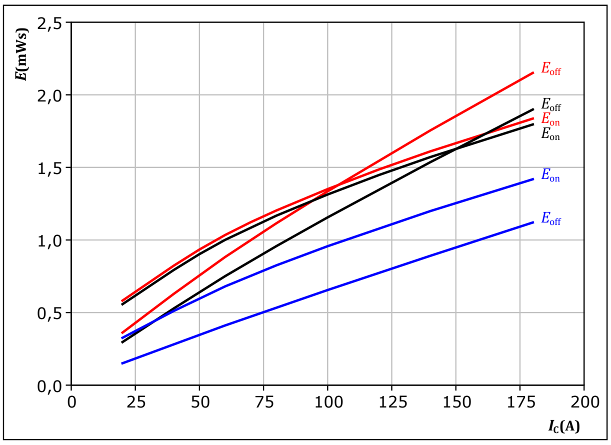


Buck Switching Characteristics

figure 18. **IGBT**

Typical switching energy losses as a function of collector current

$E = f(I_C)$



With an inductive load at

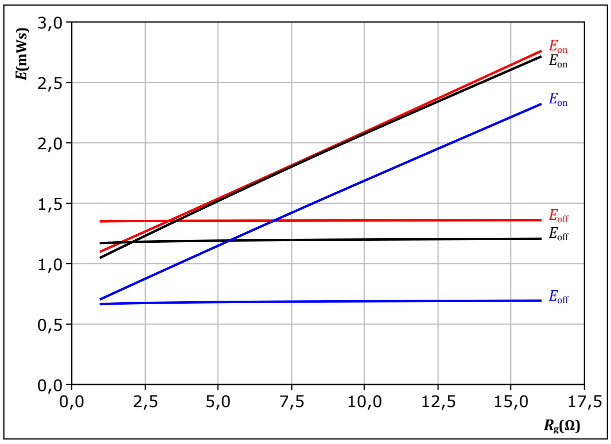
V_{CE} = 350 V
V_{GE} = ±15 V
R_{gon} = 4 Ω
R_{goff} = 4 Ω

T_j:
25 °C
125 °C
150 °C

figure 19. **IGBT**

Typical switching energy losses as a function of gate resistor

$E = f(R_g)$



With an inductive load at

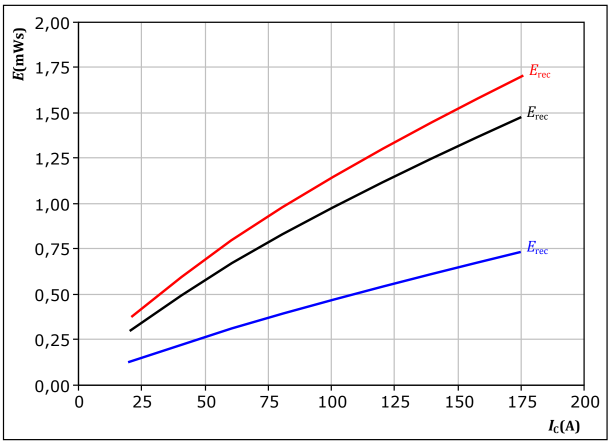
V_{CE} = 350 V
V_{GE} = ±15 V
I_C = 100 A

T_j:
25 °C
125 °C
150 °C

figure 20. **FWD**

Typical reverse recovered energy loss as a function of collector current

$E_{rec} = f(I_C)$



With an inductive load at

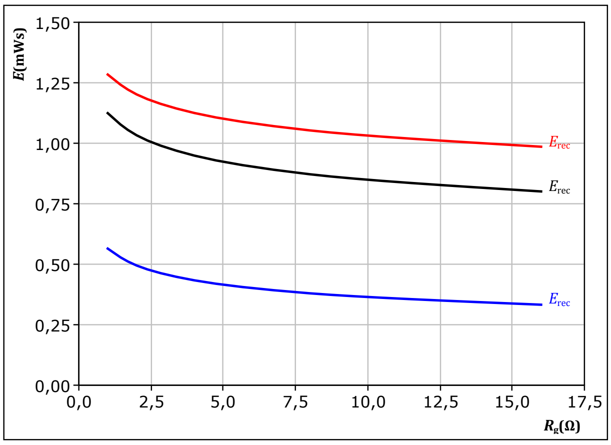
V_{CE} = 350 V
V_{GE} = ±15 V
R_{gon} = 4 Ω

T_j:
25 °C
125 °C
150 °C

figure 21. **FWD**

Typical reverse recovered energy loss as a function of gate resistor

$E_{rec} = f(R_g)$



With an inductive load at

V_{CE} = 350 V
V_{GE} = ±15 V
I_C = 100 A

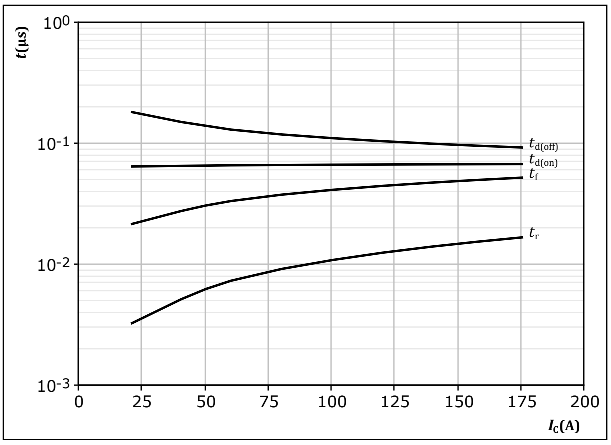
T_j:
25 °C
125 °C
150 °C

Buck Switching Characteristics

figure 22. **IGBT**

Typical switching times as a function of collector current

t = f(I_C)



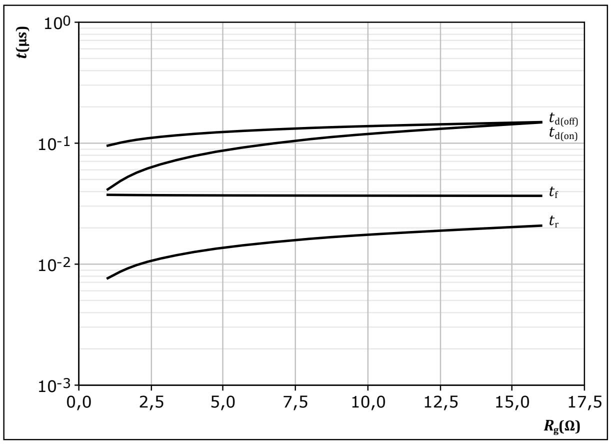
With an inductive load at

T_j =	150	°C
V_{CE} =	350	V
V_{GE} =	±15	V
R_{gon} =	4	Ω
R_{goff} =	4	Ω

figure 23. **IGBT**

Typical switching times as a function of gate resistor

t = f(R_g)



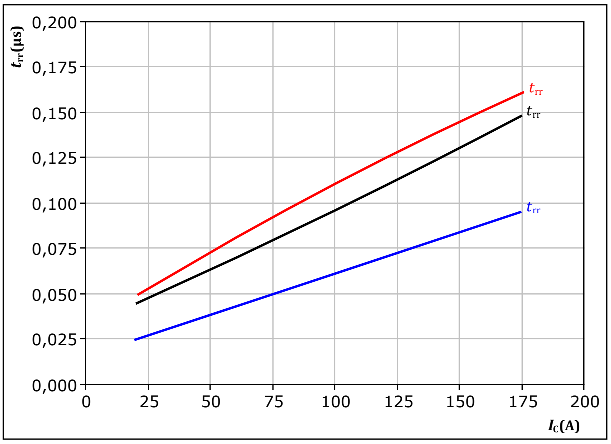
With an inductive load at

T_j =	150	°C
V_{CE} =	350	V
V_{GE} =	±15	V
I_C =	100	A

figure 24. **FWD**

Typical reverse recovery time as a function of collector current

t_{rr} = f(I_C)



With an inductive load at

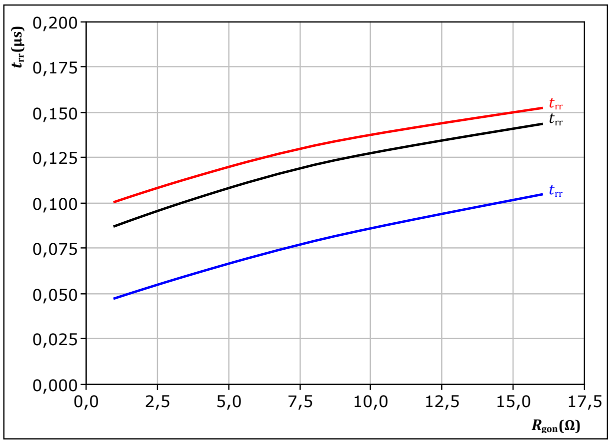
V_{CE} =	350	V
V_{GE} =	±15	V
R_{gon} =	4	Ω

T_j:
— 25 °C
— 125 °C
— 150 °C

figure 25. **FWD**

Typical reverse recovery time as a function of IGBT turn on gate resistor

t_{rr} = f(R_{gon})



With an inductive load at

V_{CE} =	350	V
V_{GE} =	±15	V
I_C =	100	A

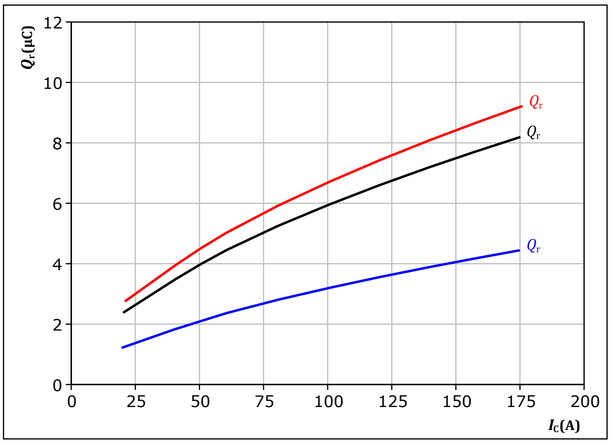
T_j:
— 25 °C
— 125 °C
— 150 °C

Buck Switching Characteristics

figure 26. **FWD**

Typical recovered charge as a function of collector current

Q_r = f(I_C)



With an inductive load at

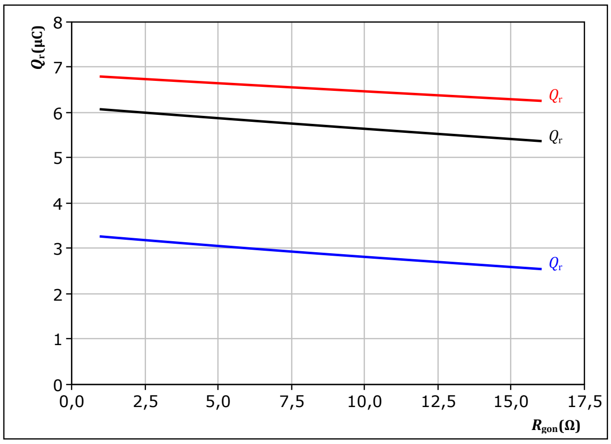
V_{CE} = 350 V
V_{GE} = ±15 V
R_{gon} = 4 Ω

T_j:
— 25 °C
— 125 °C
— 150 °C

figure 27. **FWD**

Typical recovered charge as a function of turn on gate resistor

Q_r = f(R_{gon})



With an inductive load at

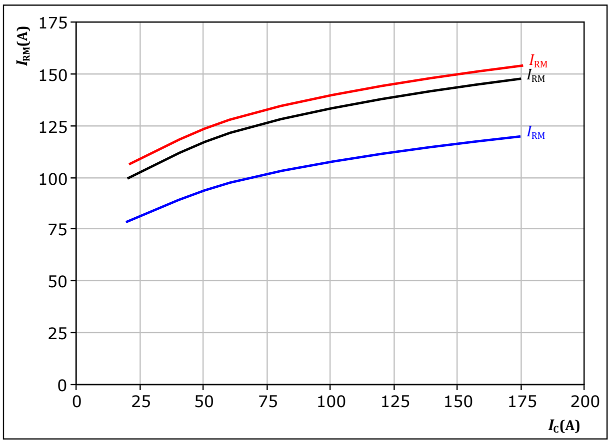
V_{CE} = 350 V
V_{GE} = ±15 V
I_C = 100 A

T_j:
— 25 °C
— 125 °C
— 150 °C

figure 28. **FWD**

Typical peak reverse recovery current as a function of collector current

I_{RM} = f(I_C)



With an inductive load at

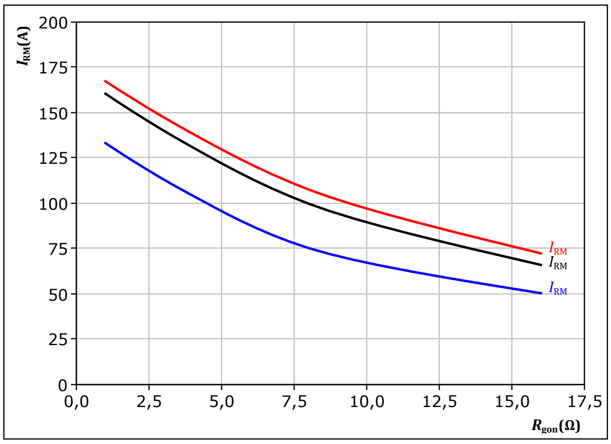
V_{CE} = 350 V
V_{GE} = ±15 V
R_{gon} = 4 Ω

T_j:
— 25 °C
— 125 °C
— 150 °C

figure 29. **FWD**

Typical peak reverse recovery current as a function of turn on gate resistor

I_{RM} = f(R_{gon})



With an inductive load at

V_{CE} = 350 V
V_{GE} = ±15 V
I_C = 100 A

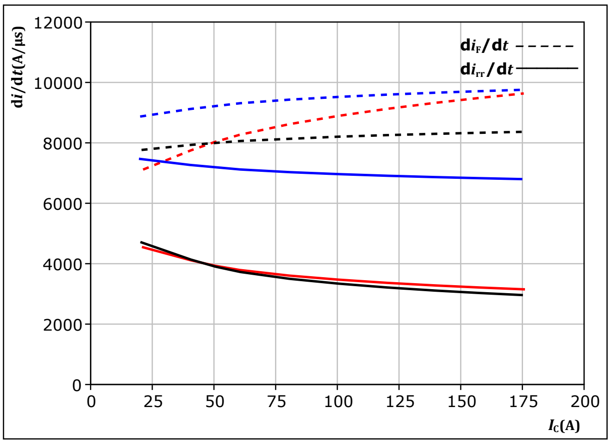
T_j:
— 25 °C
— 125 °C
— 150 °C

Buck Switching Characteristics

figure 30. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of collector current

di_F/dt, di_{rr}/dt = f(I_C)



With an inductive load at

V_{CE} = 350 V

V_{GE} = ±15 V

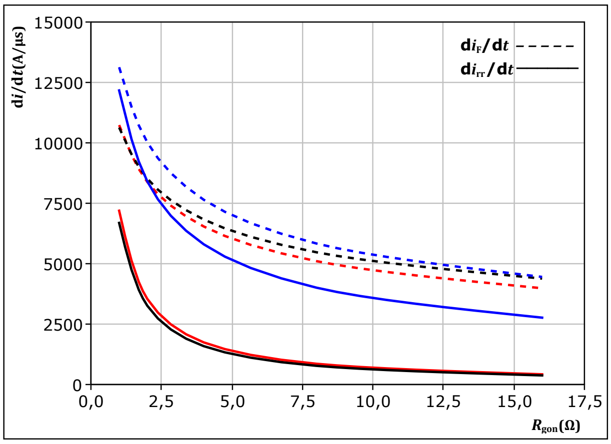
R_{gon} = 4 Ω

T_j: — 25 °C, — 125 °C, — 150 °C

figure 31. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of turn on gate resistor

di_F/dt, di_{rr}/dt = f(R_{gon})



With an inductive load at

V_{CE} = 350 V

V_{GE} = ±15 V

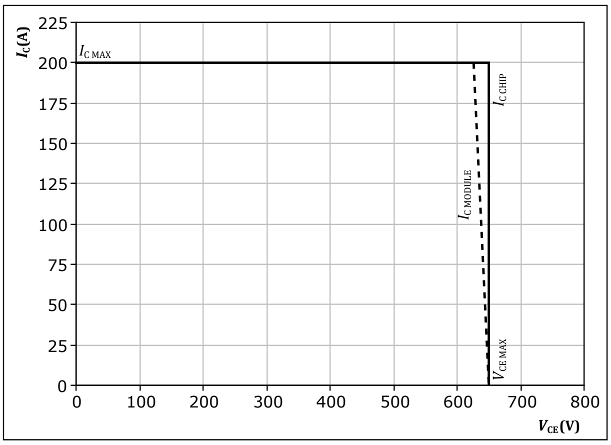
I_C = 100 A

T_j: — 25 °C, — 125 °C, — 150 °C

figure 32. **IGBT**

Reverse bias safe operating area

I_C = f(V_{CE})



At T_j = 150 °C

R_{gon} = 4 Ω

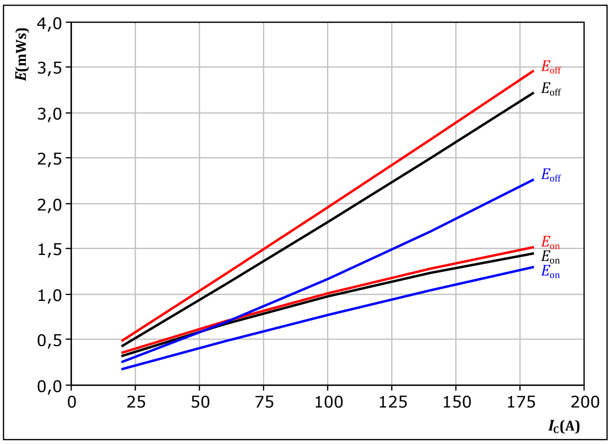
R_{goff} = 4 Ω

Boost Switching Characteristics

figure 33. **IGBT**

Typical switching energy losses as a function of collector current

$E = f(I_C)$



With an inductive load at

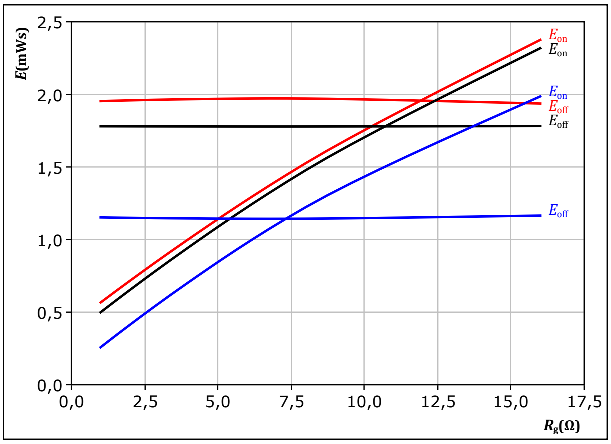
V_{CE} = 350 V
V_{GE} = ±15 V
R_{gon} = 4 Ω
R_{goff} = 4 Ω

T_j:
— 25 °C
— 125 °C
— 150 °C

figure 34. **IGBT**

Typical switching energy losses as a function of gate resistor

$E = f(R_g)$



With an inductive load at

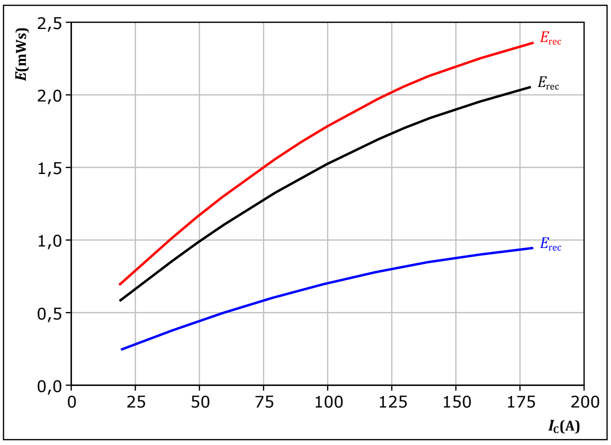
V_{CE} = 350 V
V_{GE} = ±15 V
I_C = 100 A

T_j:
— 25 °C
— 125 °C
— 150 °C

figure 35. **FWD**

Typical reverse recovered energy loss as a function of collector current

$E_{rec} = f(I_C)$



With an inductive load at

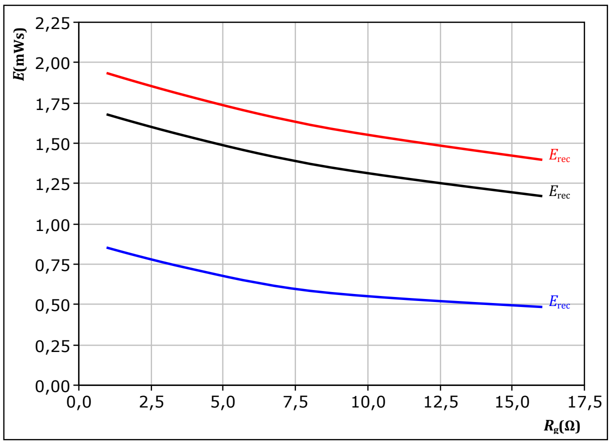
V_{CE} = 350 V
V_{GE} = ±15 V
R_{gon} = 4 Ω

T_j:
— 25 °C
— 125 °C
— 150 °C

figure 36. **FWD**

Typical reverse recovered energy loss as a function of gate resistor

$E_{rec} = f(R_g)$



With an inductive load at

V_{CE} = 350 V
V_{GE} = ±15 V
I_C = 100 A

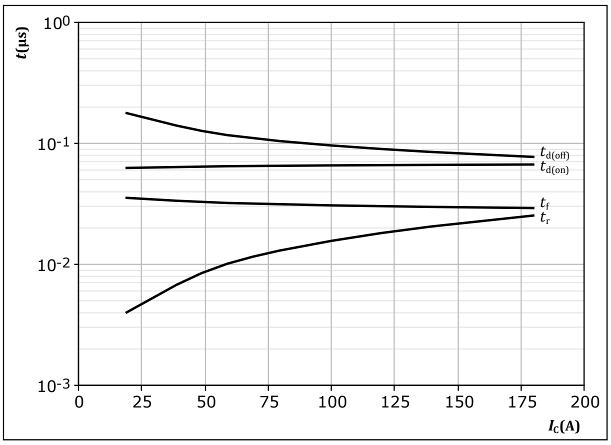
T_j:
— 25 °C
— 125 °C
— 150 °C

Boost Switching Characteristics

figure 37. **IGBT**

Typical switching times as a function of collector current

t = f(I_C)



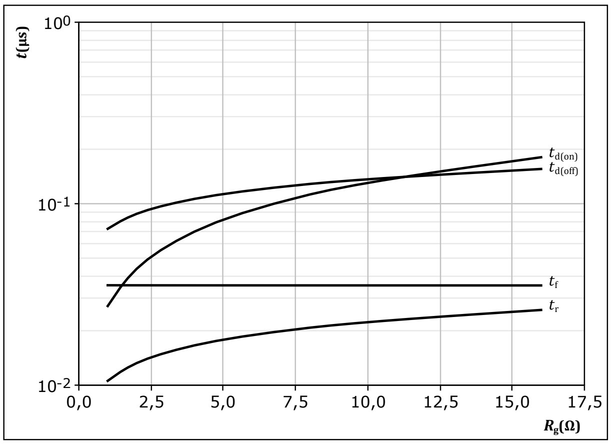
With an inductive load at

T_j = 150 °C
V_{CE} = 350 V
V_{GE} = ±15 V
R_{gon} = 4 Ω
R_{goff} = 4 Ω

figure 38. **IGBT**

Typical switching times as a function of gate resistor

t = f(R_g)



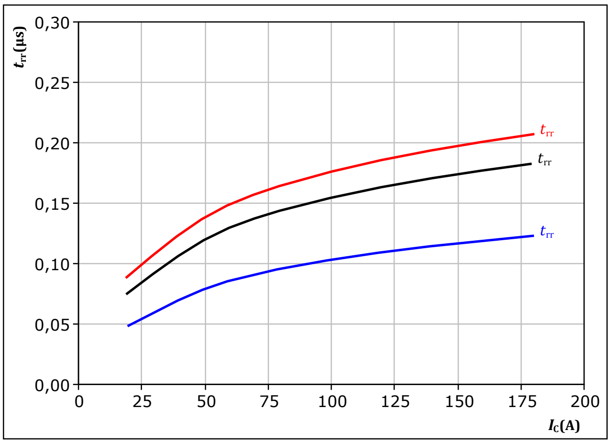
With an inductive load at

T_j = 150 °C
V_{CE} = 350 V
V_{GE} = ±15 V
I_C = 100 A

figure 39. **FWD**

Typical reverse recovery time as a function of collector current

t_{rr} = f(I_C)



With an inductive load at

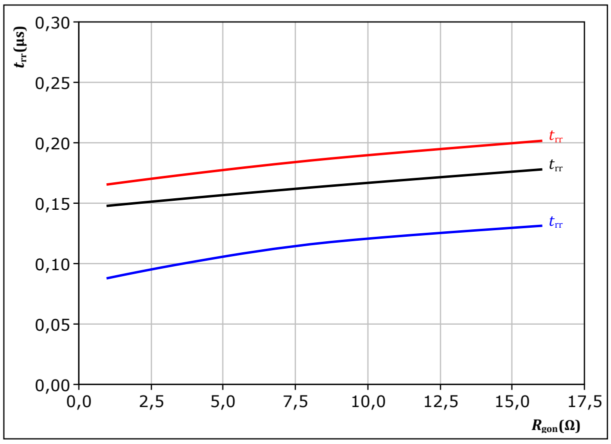
V_{CE} = 350 V
V_{GE} = ±15 V
R_{gon} = 4 Ω

T_j:
— 25 °C
— 125 °C
— 150 °C

figure 40. **FWD**

Typical reverse recovery time as a function of IGBT turn on gate resistor

t_{rr} = f(R_{gon})



With an inductive load at

V_{CE} = 350 V
V_{GE} = ±15 V
I_C = 100 A

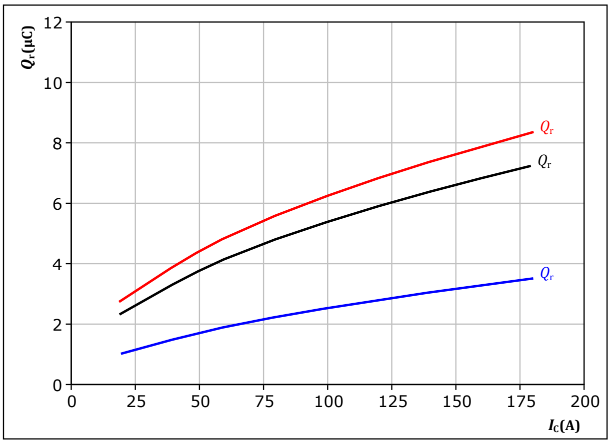
T_j:
— 25 °C
— 125 °C
— 150 °C

Boost Switching Characteristics

figure 41. **FWD**

Typical recovered charge as a function of collector current

Q_r = f(I_C)



With an inductive load at

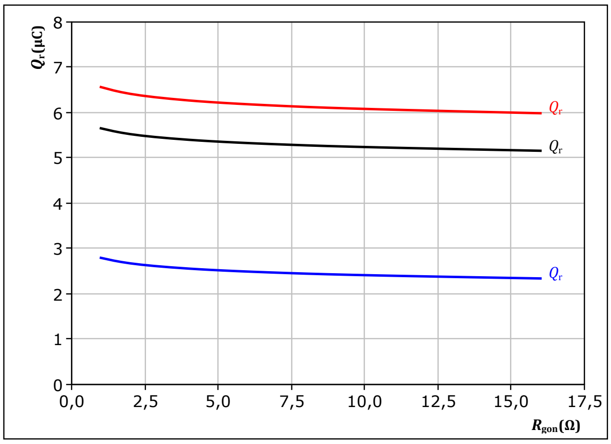
V_{CE} = 350 V
V_{GE} = ±15 V
R_{gon} = 4 Ω

T_j:
— 25 °C
— 125 °C
— 150 °C

figure 42. **FWD**

Typical recovered charge as a function of turn on gate resistor

Q_r = f(R_{gon})



With an inductive load at

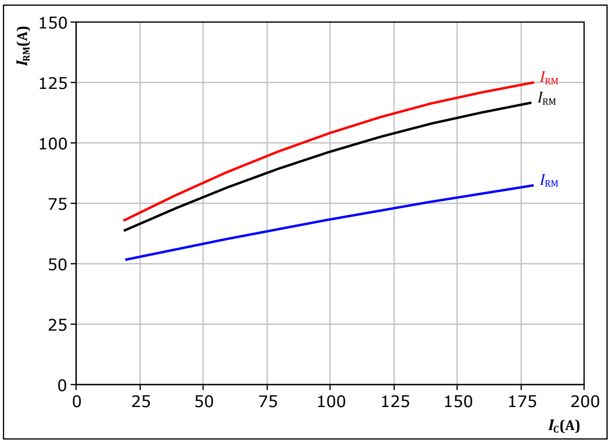
V_{CE} = 350 V
V_{GE} = ±15 V
I_C = 100 A

T_j:
— 25 °C
— 125 °C
— 150 °C

figure 43. **FWD**

Typical peak reverse recovery current as a function of collector current

I_{RM} = f(I_C)



With an inductive load at

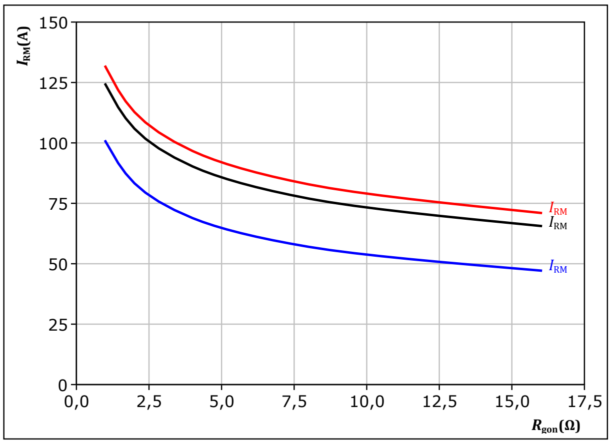
V_{CE} = 350 V
V_{GE} = ±15 V
R_{gon} = 4 Ω

T_j:
— 25 °C
— 125 °C
— 150 °C

figure 44. **FWD**

Typical peak reverse recovery current as a function of turn on gate resistor

I_{RM} = f(R_{gon})



With an inductive load at

V_{CE} = 350 V
V_{GE} = ±15 V
I_C = 100 A

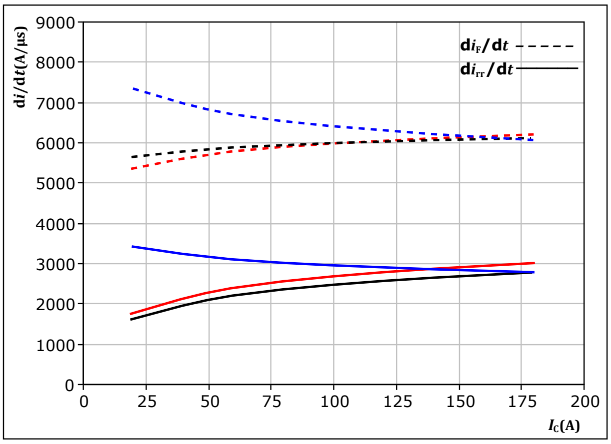
T_j:
— 25 °C
— 125 °C
— 150 °C

Boost Switching Characteristics

figure 45. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of collector current

$di_F/dt,\ di_{rr}/dt = f(\ I_C)$



With an inductive load at

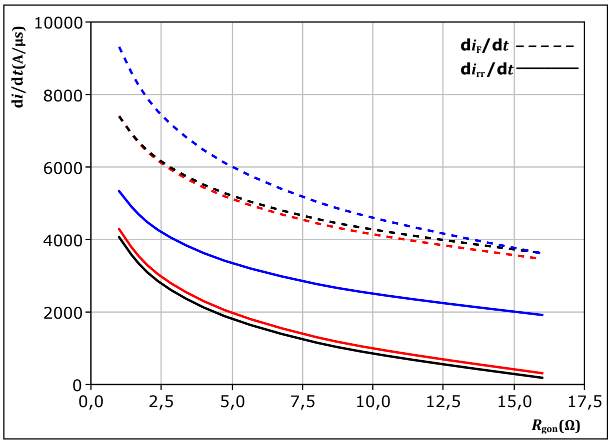
V_{CE} = 350 V
V_{GE} = ±15 V
R_{gon} = 4 Ω

T_j:
25 °C
125 °C
150 °C

figure 46. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of turn on gate resistor

$di_F/dt,\ di_{rr}/dt = f(\ R_{gon})$



With an inductive load at

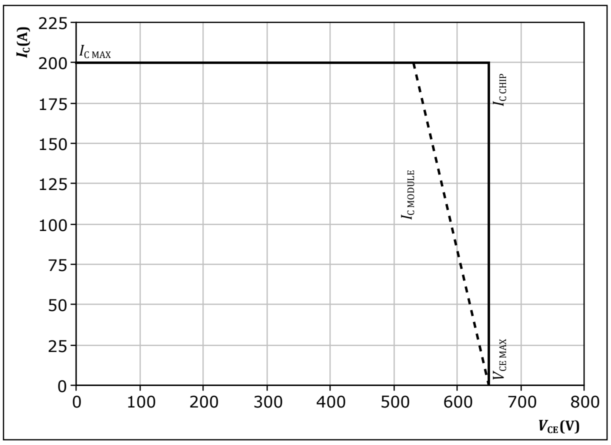
V_{CE} = 350 V
V_{GE} = ±15 V
I_C = 100 A

T_j:
25 °C
125 °C
150 °C

figure 47. **IGBT**

Reverse bias safe operating area

$I_C = f(\ V_{CE})$



At T_j = 150 °C
R_{gon} = 4 Ω
R_{goff} = 4 Ω

Switching Definitions

figure 48. **IGBT**

Turn-off Switching Waveforms & definition of t_{doff}, t_{Eoff} (t_{tEoff} **= integrating time for** E_{off})

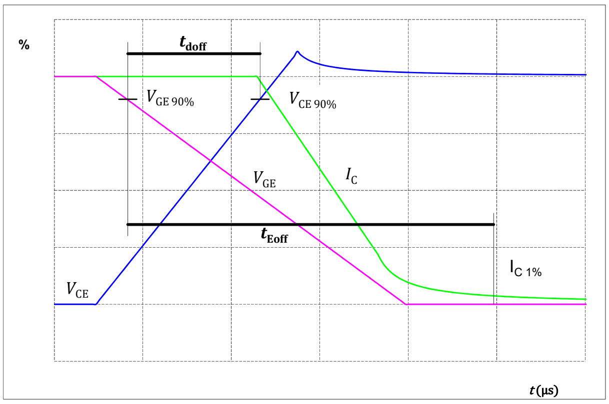


figure 49. **IGBT**

Turn-on Switching Waveforms & definition of t_{don}, t_{Eon} (t_{Eon} **= integrating time for** E_{on})

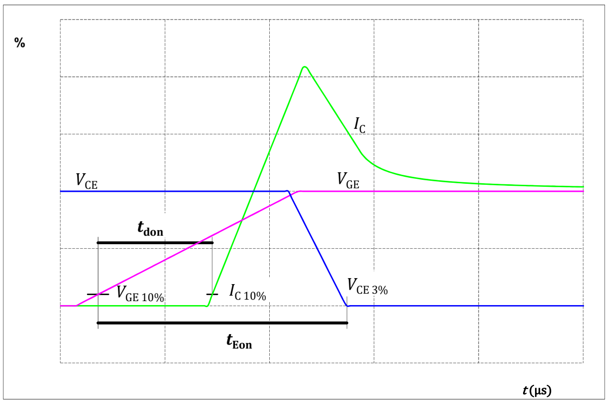


figure 50. **IGBT**

Turn-off Switching Waveforms & definition of t_f

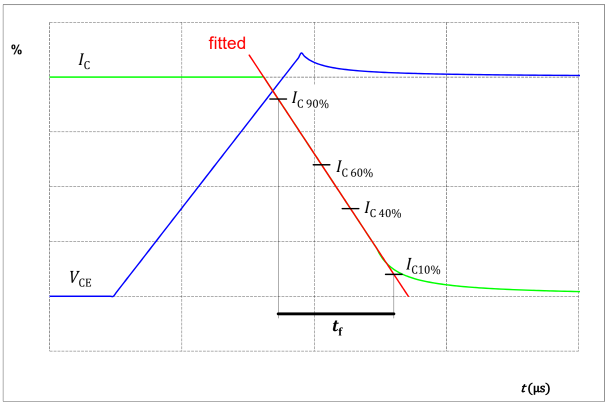
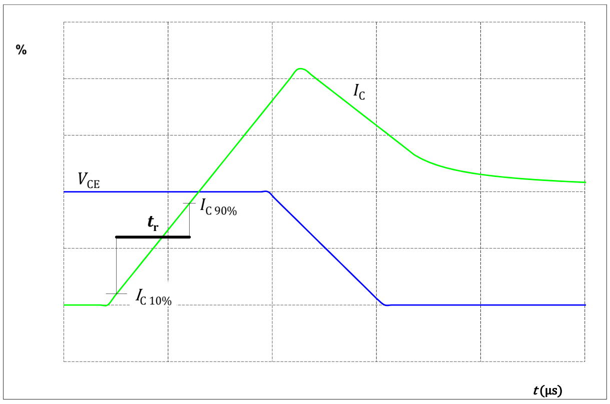


figure 51. **IGBT**

Turn-on Switching Waveforms & definition of t_r



Switching Definitions

figure 52. **FWD**

Turn-off Switching Waveforms & definition of t_{rr}

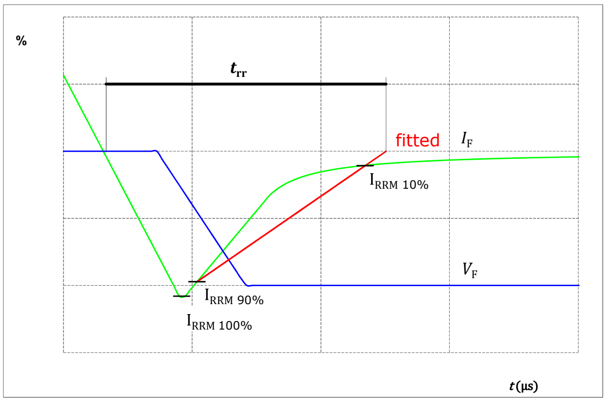
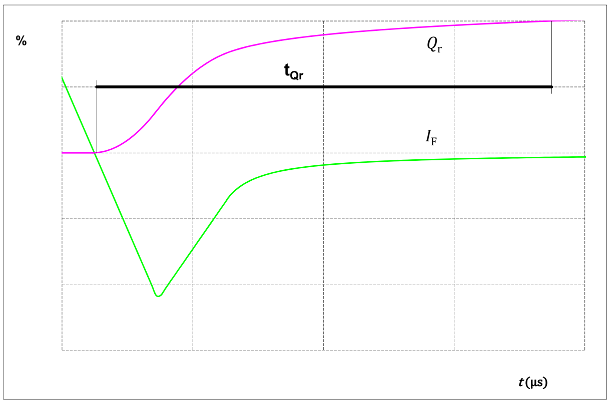


figure 53. **FWD**

Turn-on Switching Waveforms & definition of t_{Qr} (t_{Qr} = integrating time for Q_r)



Ordering Code

Version	Ordering Code
Without thermal paste	10-FZ07NIA100S502-P927F58
With thermal paste	10-FZ07NIA100S502-P927F58-/3/

Marking

<table>
<tr><td rowspan="4"> </td><td rowspan="2">Text</td><td colspan="2">Name</td><td>Date code</td><td>UL & VIN</td><td>Lot</td><td>Serial</td></tr>
<tr><td colspan="2">NN-NNNNNNNNNNNNNN-TTTTTTVV</td><td>WWYY</td><td>UL VIN</td><td>LLLLL</td><td>SSSS</td></tr>
<tr><td rowspan="2">Datamatrix</td><td>Type&Ver</td><td>Lot number</td><td>Serial</td><td>Date code</td><td></td><td></td></tr>
<tr><td>TTTTTTTVV</td><td>LLLLL</td><td>SSSS</td><td>WWYY</td><td></td><td></td></tr>
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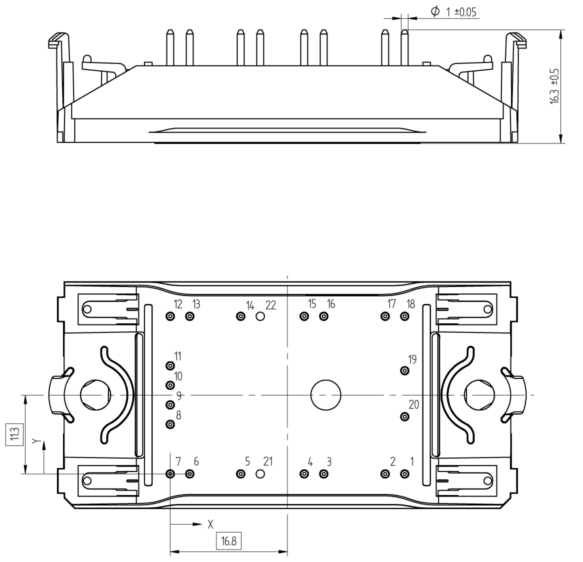
Outline

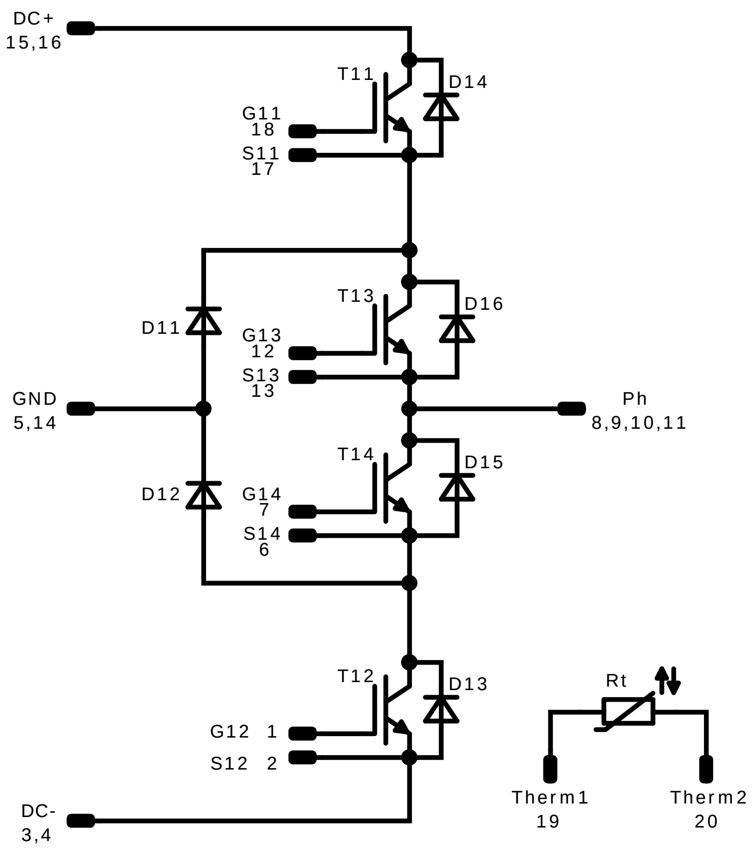
Pin table [mm]

Pin	X	Y	Function
1	33,6	0	G12
2	30,8	0	S12
3	22	0	DC-
4	19,2	0	DC-
5	10,1	0	GND
6	2,8	0	S14
7	0	0	G14
8	0	7,1	Ph
9	0	9,9	Ph
10	0	12,7	Ph
11	0	15,5	Ph
12	0	22,6	G13
13	2,8	22,6	S13
14	10,1	22,6	GND
15	19,2	22,6	DC+
16	22	22,6	DC+
17	30,8	22,6	S11
18	33,6	22,6	G11
19	33,6	14,8	Therm1
20	33,6	8,2	Therm2
21	not assembled		
22	not assembled		



Tolerance of pinpositions: ±0,5mm at the end of pins
Dimension of coordinate axis is only offset without tolerance

Pinout



Identification

ID	Component	Voltage	Current	Function	Comment
T11, T12	IGBT	650 V	100 A	Buck Switch	
D11, D12	FWD	650 V	100 A	Buck Diode	
T13, T14	IGBT	650 V	100 A	Boost Switch	
D13, D14	FWD	650 V	100 A	Boost Diode	
D15, D16	FWD	650 V	100 A	Boost Sw. Inv. Diode	
Rt	NTC			Thermistor	

Packaging instruction				
Standard packaging quantity (SPQ) 135	>SPQ	Standard	<SPQ	Sample

Handling instruction
Handling instructions for *flow* 0 packages see vincotech.com website.

Package data
Package data for *flow* 0 packages see vincotech.com website.

UL recognition and file number
This device is certified according to UL 1557 standard, UL file number E192116. For more information see vincotech.com website.

Document No.:	Date:	Modification:	Pages
10-FZ07NIA100S502-P927F58-D1-14	23 Apr. 2020		

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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